Silicon Controlled Rectifiers
Reverse Blocking Triode Thyristors

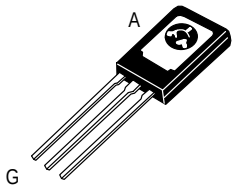
MCR106 Series*

***Motorola preferred devices except MCR106–3**

SCRs
4 AMPERES RMS
60 thru 600 VOLTS

PNPN devices designed for high volume consumer applications such as temperature, light and speed control; process and remote control, and warning systems where reliability of operation is important.

- Glass-Passivated Surface for Reliability and Uniformity
- Power Rated at Economical Prices
- Practical Level Triggering and Holding Characteristics
- Flat, Rugged, Thermopad Construction for Low Thermal Resistance, High Heat Dissipation and Durability



CASE 77-08
(TO-225AA)
STYLE 2

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted.)

Rating	Symbol	Value	Unit
Peak Repetitive Forward and Reverse Blocking Voltage(1) (T_J = 110°C, R_{GK} = 1 kΩ)	V_{DRM} and V_{RRM}		Volts
MCR106-2		60	
MCR106-3		100	
MCR106-4		200	
MCR106-6		400	
MCR106-8		600	
RMS Forward Current (All Conduction Angles)	$I_{T(RMS)}$	4	Amps
Average Forward Current T_C = 93°C T_A = 30°C or	$I_{T(AV)}$	2.55	Amps
Peak Non-repetitive Surge Current (1/2 Cycle, 60 Hz, T_J = –40 to +110°C)	I_{TSM}	25	Amps
Circuit Fusing Considerations (t = 8.3 ms)	I^2t	2.6	A^2s
Peak Gate Power	P_{GM}	0.5	Watt
Average Gate Power	$P_{G(AV)}$	0.1	Watt
Peak Forward Gate Current	I_{GM}	0.2	Amp
Peak Reverse Gate Voltage	V_{RGM}	6	Volts
Operating Junction Temperature Range	T_J	–40 to +110	°C

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded. (cont.)

Preferred devices are Motorola recommended choices for future use and best overall value.

MAXIMUM RATINGS — continued

Rating	Symbol	Value	Unit
Storage Temperature Range	T_{stg}	–40 to +150	°C
Mounting Torque(1)	—	6	in. lb.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	3	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	75	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C and R_{GK} = 1000 Ohms unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Peak Forward or Reverse Blocking Current (V_{AK} = Rated V_{DRM} or V_{RRM}) T_J = 25°C T_J = 110°C	I_{DRM}, I_{RRM}	 — —	 — —	 10 200	 µA µA
Forward “On” Voltage (I_{TM} = 4 A Peak)	V_{TM}	—	—	2	Volts
Gate Trigger Current (Continuous dc)(2) (V_{AK} = 7 Vdc, R_L = 100 Ohms) (V_{AK} = 7 Vdc, R_L = 100 Ohms, T_C = –40°C)	I_{GT}	 — —	 — —	 200 500	µA
Gate Trigger Voltage (Continuous dc) (V_{AK} = 7 Vdc, R_L = 100 Ohms, T_C = 25°C)	V_{GT}	—	—	1	Volts
Gate Non-Trigger Voltage (V_{AK} = Rated V_{DRM}, R_L = 100 Ohms, T_J = 110°C)	V_{GD}	0.2	—	—	Volts
Holding Current (V_{AK} = 7 Vdc, T_C = 25°C)	I_H	—	—	5	mA
Forward Voltage Application Rate (T_J = 110°C)	dv/dt	—	10	—	V/µs

1. Torque rating applies with use of compression washer (B52200-F006 or equivalent). Mounting torque in excess of 6 in. lb. does not appreciably lower case-to-sink thermal resistance. Anode lead and heatsink contact pad are common. (See AN209B).
   For soldering purposes (either terminal connection or device mounting), soldering temperatures shall not exceed +200°C. For optimum results, an activated flux (oxide removing) is recommended.
2. R_{GK} current is not included in measurement.

CURRENT DERATING

FIGURE 1 – MAXIMUM CASE TEMPERATURE

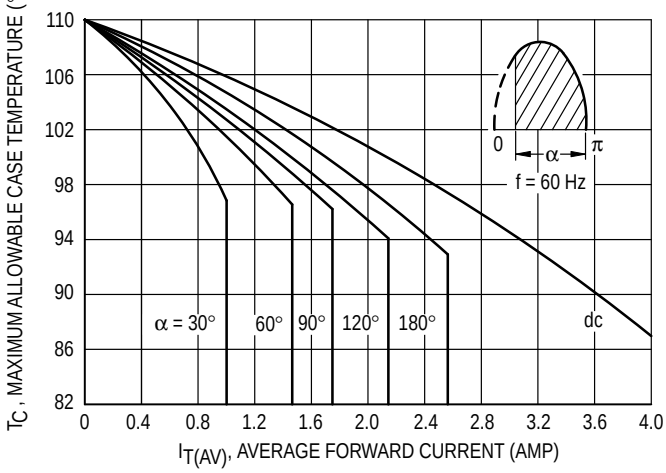
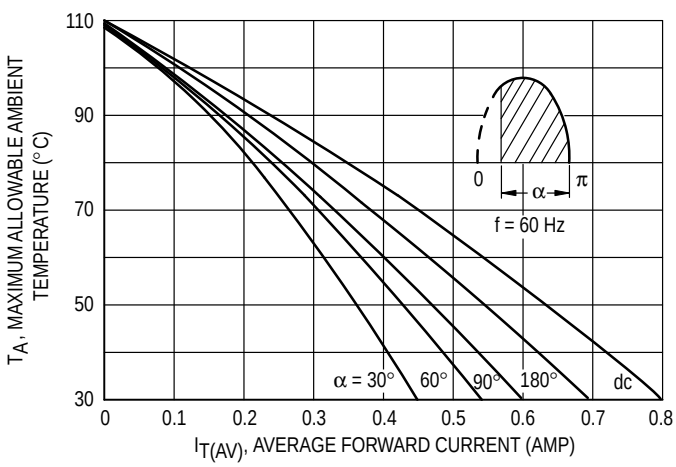
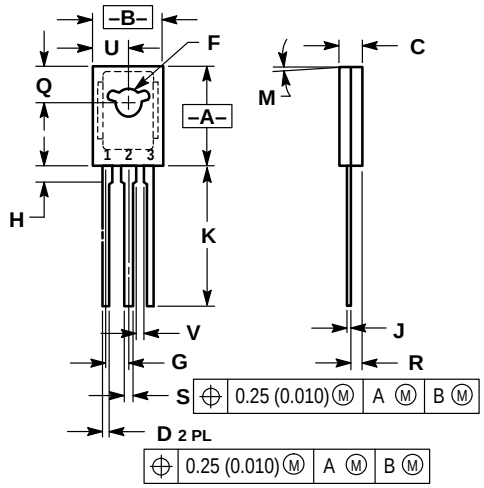


FIGURE 2 – MAXIMUM AMBIENT TEMPERATURE



PACKAGE DIMENSIONS



STYLE 2:
PIN 1. CATHODE
2. ANODE
3. GATE

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.055	1.15	1.39
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	—	1.02	—

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(TO–225AA)

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